

International  
**IR** Rectifier

**SAFEIR** Series  
70TPS..PbF

PHASE CONTROL SCR  
Lead-Free ("PbF" suffix)



$$V_T < 1.4V @ 100A$$

$$I_{TSM} = 1400A$$

$$V_{RRM} = 1200 \text{ e } 1600V$$

#### Description/ Features

The 70TPS..PbF **SAFEIR** series of silicon controlled rectifiers are specifically designed for high and medium power switching and phase control applications.

Typical applications are in input rectification (soft start) or AC-Switches or high current crow-bar as well as others phase-control circuits.

These products are designed to be used with International Rectifier input diodes, switches and output rectifiers which are available in identical package outlines.

#### Major Ratings and Characteristics

Characteristics	Values	Units
$I_{T(AV)}$ Sinusoidal waveform	70	A
$I_{RMS}$ (*)	75	A
$V_{RRM}/V_{DRM}$ Range	1200e1600	V
$I_{TSM}$	1400	A
$V_T$ @ 100 A, $T_J = 25^\circ\text{C}$	1.4	V
dv/dt	500	V/ $\mu\text{s}$
di/dt	150	A/ $\mu\text{s}$
$T_J$	-40 to 125	$^\circ\text{C}$

(\*) Lead current limitation

#### Package Outline



Super-247

## Voltage Ratings

Part Number	$V_{RRM}/V_{DRM}$ , max. repetitive peak and off-state voltage V	$V_{RSM}$ , maximum non repetitive peak reverse voltage V	$I_{RRM}/I_{DRM}$ 125°C mA
70TPS12PbF	1200	1300	15
70TPS16PbF	1600	1700	

## Absolute Maximum Ratings

Parameters	70TPS..	Units	Conditions	
$I_{T(AV)}$ Max. Average On-state Current	70	A	@ $T_C = 82^\circ\text{C}$ , 180° conduction half sine wave	
$I_{T(RMS)}$ Max. Continuous RMS On-state Current As AC switch	75		Lead current limitation	
$I_{TSM}$ Max. Peak One Cycle Non-Repetitive Surge Current	1200 1400	A	10ms Sine pulse, rated $V_{RRM}$ applied	Initial $T_J = T_J \text{ max.}$
			10ms Sine pulse, no voltage reapplied	
$I^2t$ Max. $I^2t$ for Fusing	7200 10200	$A^2s$	10ms Sine pulse, rated $V_{RRM}$ applied	
			10ms Sine pulse, no voltage reapplied	
$I^2\sqrt{t}$ Max. $I^2\sqrt{t}$ for Fusing	102000	$A^2\sqrt{s}$	t = 0.1 to 10ms, no voltage reapplied	
$V_{T(TO)1}$ Low Level Value of Threshold Voltage	0.916	V	$T_J = 125^\circ\text{C}$	
$V_{T(TO)2}$ High Level Value of Threshold Voltage	1.21			
$r_{t1}$ Low Level Value of On-state Slope Resistance	4.138			
$r_{t2}$ High Level Value of On-state Slope Resistance	3.43			
$V_{TM}$ Max. Peak On-state Voltage	1.4	V	@ 100A, $T_J = 25^\circ\text{C}$	
di/dt Max. Rate of Rise of Turned-on Current	150	A/μs	$T_J = 25^\circ\text{C}$	
$I_H$ Max. Holding Current	200	mA	$T_J = 25^\circ\text{C}$	
$I_L$ Max. Latching Current	400			
$I_{RRM}/I_{DRM}$ Max. Reverse and Direct Leakage Current	1.0 15	mA	$T_J = 25^\circ\text{C}$	$V_R = \text{rated } V_{RRM}/V_{DRM}$
			$T_J = 125^\circ\text{C}$	
dv/dt Max. Rate of Rise	500	V/μs	$T_J = 125^\circ\text{C}$	

### Triggering

Parameters	70TPS..	Units	Conditions		
$P_{GM}$ Max. peak Gate Power	10	W	$t = 30\mu s$		
$P_{G(AV)}$ Max. average Gate Power	2.5				
$I_{GM}$ Max. peak Gate Current	2.5	A			
$-V_{GM}$ Max. peak negative Gate Voltage	10	V	Anode supply = 6V resistive load		
$V_{GT}$ Max. required DC Gate Voltage to trigger	4.0				$T_J = -40^\circ C$
	1.5				$T_J = 25^\circ C$
	1.1				$T_J = 125^\circ C$
$I_{GT}$ Max. required DC Gate Current to trigger	270	mA	$T_J = -40^\circ C$		
	100		$T_J = 25^\circ C$		
	80		$T_J = 125^\circ C$		
$V_{GD}$ Max. DC Gate Voltage not to trigger	0.25	V	$T_J = 125^\circ C, V_{DRM} = \text{rated value}$		
$I_{GD}$ Max. DC Gate Current not to trigger	6	mA			

### Thermal-Mechanical Specifications

Parameters	70TPS..	Units	Conditions		
$T_J$ Max. Junction Temperature Range	- 40 to 125	°C			
$T_{stg}$ Max. Storage Temperature Range	- 40 to 150				
$R_{thJC}$ Max. Thermal Resistance Junction to Case	0.27	°C/W	DC operation		
$R_{thJA}$ Max. Thermal Resistance Junction to Ambient	40		Mounting surface, smooth and greased		
$R_{thCS}$ Max. Thermal Resistance Case to Heatsink	0.2				
wt Approximate Weight	6 (0.21)	g (oz.)			
T Mounting Torque	Min.	6 (5)	Kg-cm (lbf-in)		
	Max.	12 (10)			
Case Style	Super-247				
Marking Device	70TPS16				

### $\Delta R$ Conduction (per Junction)

(The following table shows the increment of thermal resistance  $R_{thJC}$  when devices operate at different conduction angles than DC)

Device	Sine half wave conduction					Rect. wave conduction					Units
	180°	120°	90°	60°	30°	180°	120°	90°	60°	30°	
70TPS	0.078	0.092	0.117	0.172	0.302	0.053	0.092	0.125	0.180	0.306	°C/W

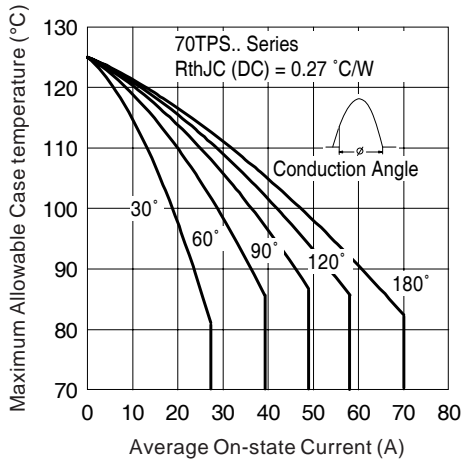


Fig. 1 - Current Rating Characteristics

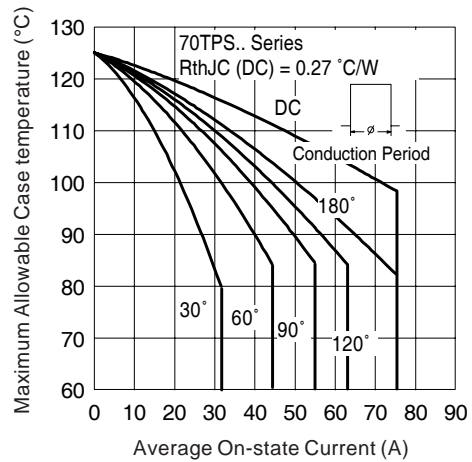


Fig. 2 - Current Rating Characteristics

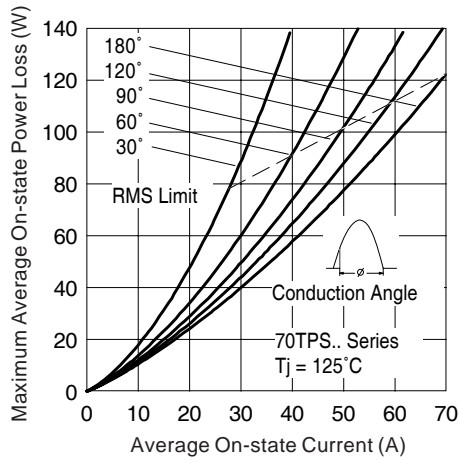


Fig. 3 - On-state Power Loss Characteristics

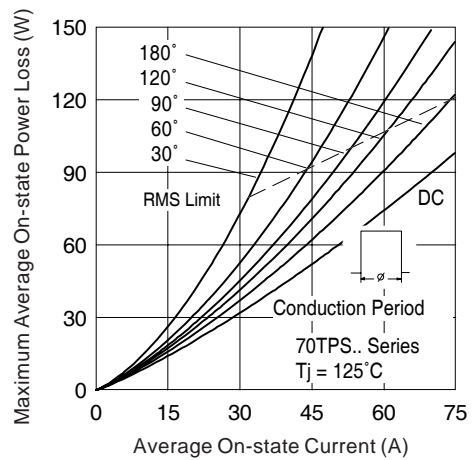


Fig. 4 - On-state Power Loss Characteristics

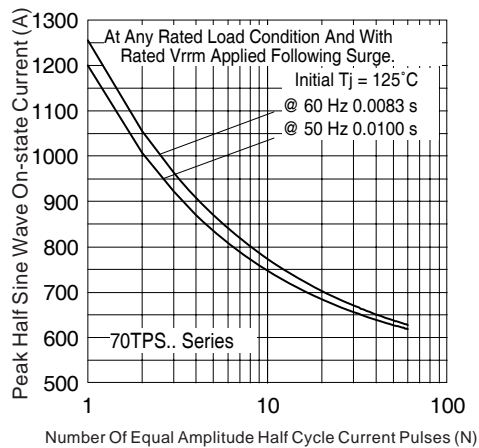


Fig. 5 - Maximum Non-Repetitive Surge Current

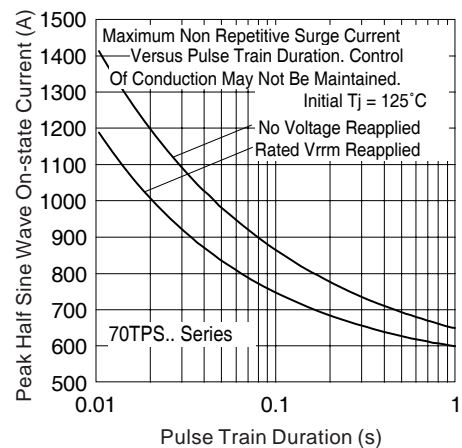


Fig. 6 - Maximum Non-Repetitive Surge Current

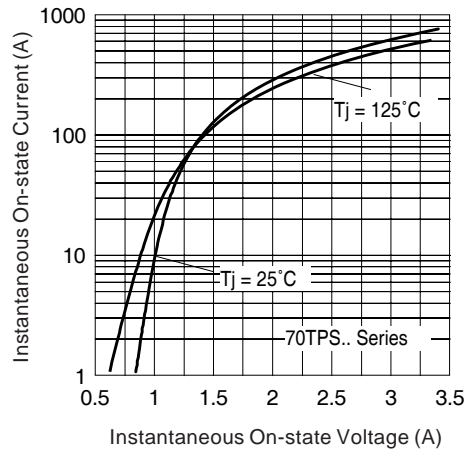


Fig. 7 - On-state Voltage Drop Characteristics

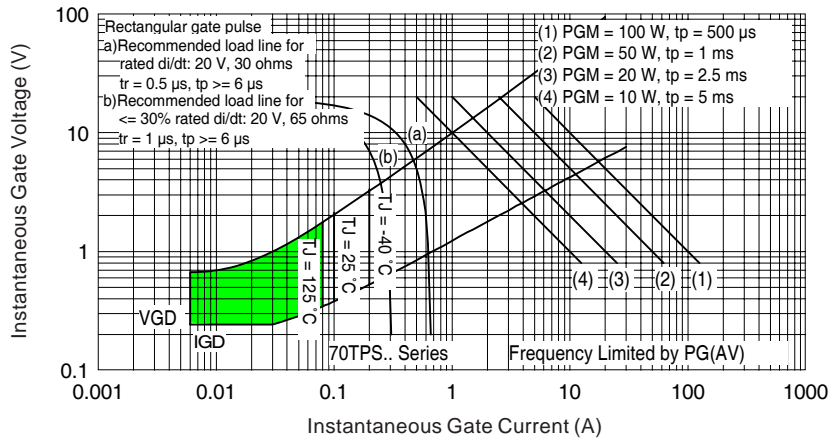


Fig. 8 - Gate Characteristics

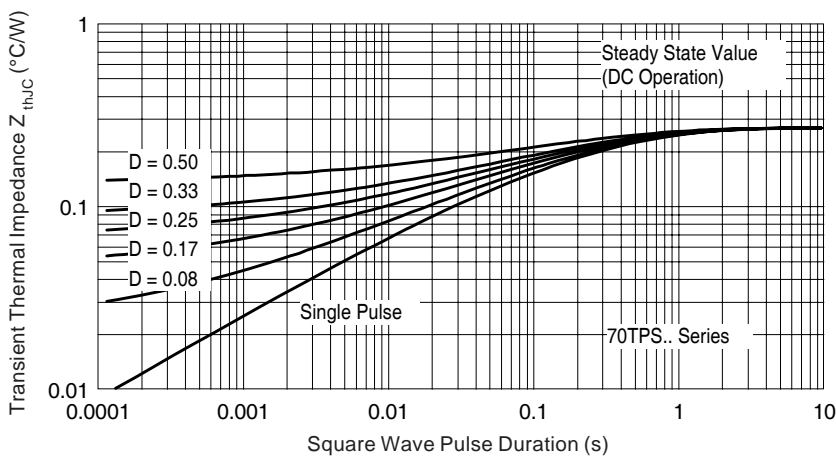
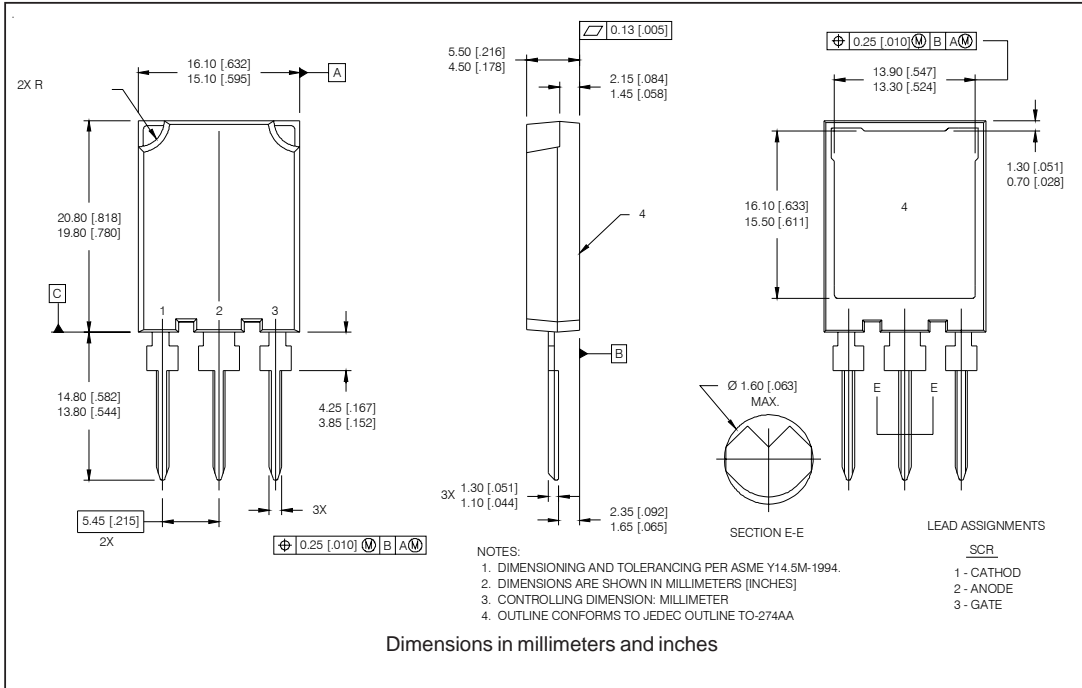
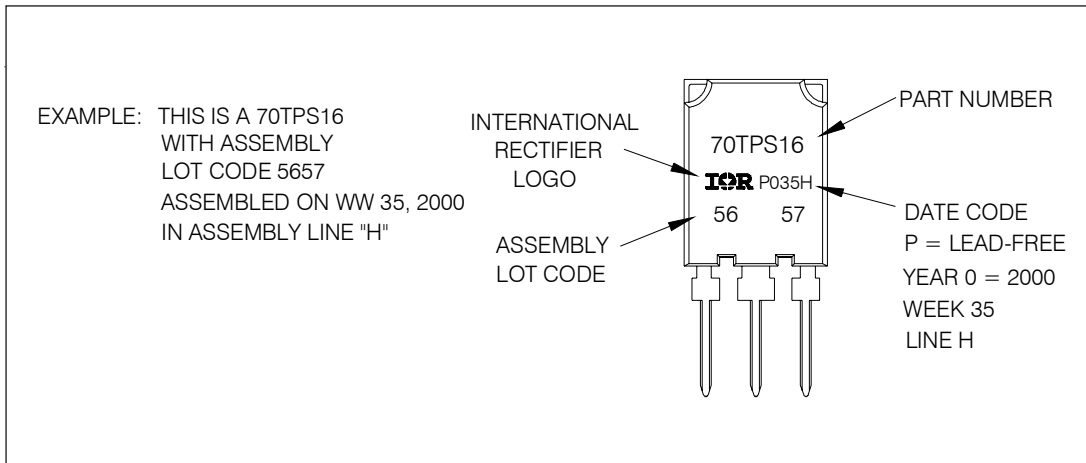


Fig. 9 - Thermal Impedance  $Z_{thJC}$  Characteristics

Outline Table



Marking Information



Ordering Information Table

Device Code					
<b>70</b>	<b>T</b>	<b>P</b>	<b>S</b>	<b>16</b>	<b>PbF</b>
①	②	③	④	⑤	⑥

<p><b>1</b> - Current Rating (70 = 70A)</p> <p><b>2</b> - Circuit Configuration: T = Thyristor</p> <p><b>3</b> - Package: P = Super-247</p> <p><b>4</b> - Type of Silicon: S = Standard Recovery Rectifier</p> <p><b>5</b> - Voltage code: Code x 100 = <math>V_{RRM}</math></p> <p><b>6</b> - • none = Standard Production • PbF = Lead-Free</p>	<div style="border: 1px solid black; padding: 5px; width: fit-content;"> <p>2 (A)</p> <p>1 (K) (G) 3</p> </div> <div style="border: 1px solid black; padding: 5px; width: fit-content;"> <p>12 = 1200V 16 = 1600V</p> </div>
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Data and specifications subject to change without notice.  
 This product has been designed for Industrial Level.  
 Qualification Standards can be found on IR's Web site.



## Notice

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